P-Channel Enhancement-Mode Vertical DMOS FET

Features

- Low threshold (-2.4V max.)
- High input impedance
- Low input capacitance (85pF typ.)
- Fast switching speeds
- Low on-resistance
- Free from secondary breakdown
- Low input and output leakage

Applications

- Logic level interfaces – ideal for TTL and CMOS
- Solid state relays
- Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- Telecom switches

General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package	Wafer / Die Options		
	TO-92	NW (Die in wafer form)	NJ (Die on adhesive tape)	ND (Die in waffle pack)
TP0620	TP0620N3-G	TP2520NW	TP2520NJ	TP2520ND

For packaged products, -G indicates package is RoHS compliant ('Green'). Devices in Wafer / Die form are RoHS compliant ('Green'). Refer to Die Specification VF25 for layout and dimensions.

Product Summary

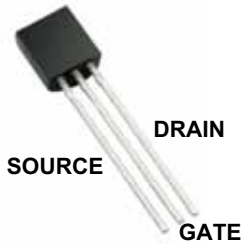
Device	BV_{DSS}/BV_{DGS} (V)	$R_{DS(ON)}$ (max) (Ω)	$I_{D(ON)}$ (min) (A)	$V_{GS(th)}$ (max) (V)
TP0620N3-G	-200	12	-0.75	-2.4

Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV_{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configuration



TO-92 (N3)

Product Marking

YY = Year Sealed
WW = Week Sealed
_____ = "Green" Packaging

Package may or may not include the following marks: Si or

TO-92 (N3)

Thermal Characteristics

Package	I_D (continuous)† (mA)	I_D (pulsed) (A)	Power Dissipation @T_C = 25°C (W)	θ_{jc} (°C/W)	θ_{ja} (°C/W)	I_{DR}† (mA)	I_{DRM} (A)
TO-92	-175	-0.8	1.0	125	170	-175	-0.8

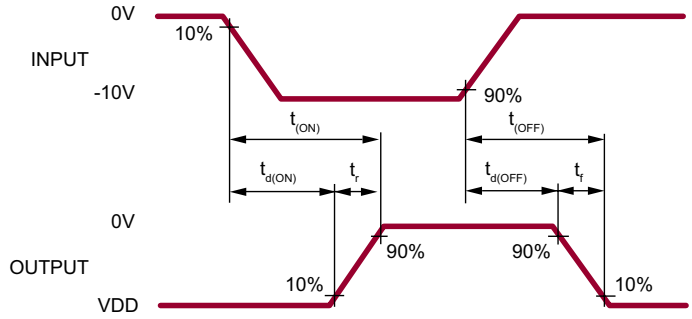
Notes:
† I_D (continuous) is limited by max rated T_j .

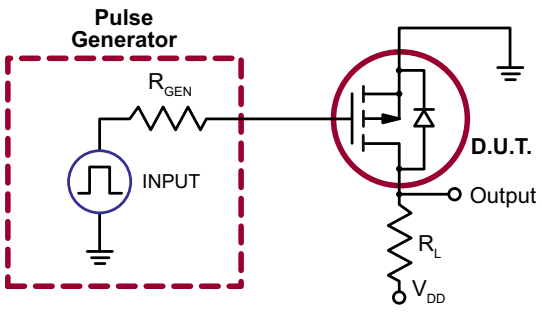
Electrical Characteristics *(T_A = 25°C unless otherwise specified)*

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	-200	-	-	V	V_{GS} = 0V, I_D = -2.0mA
$V_{GS(th)}$	Gate threshold voltage	-1.0	-	-2.4	V	V_{GS} = V_{DS}, I_D= -1.0mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-	-4.5	mV/°C	V_{GS} = V_{DS}, I_D= -1.0mA
I_{GSS}	Gate body leakage	-	-	-100	nA	V_{GS} = ± 20V, V_{DS} = 0V
I_{DSS}	Zero gate voltage drain current	-	-	-10	µA	V_{GS} = 0V, V_{DS} = Max Rating
		-	-	-1.0	mA	V_{DS} = 0.8 Max Rating, V_{GS} = 0V, T_A = 125°C
$I_{D(ON)}$	ON-state drain current	-0.25	-	-	A	V_{GS} = -5.0V, V_{DS} = -25V
		-0.75	-	-		V_{GS} = -10V, V_{DS} = -25V
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	9.0	15	Ω	V_{GS} = -5.0V, I_D = -100mA
		-	7.0	12		V_{GS} = -10V, I_D = -200mA
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.7	%/°C	V_{GS} = -10V, I_D = -200mA
G_{FS}	Forward transductance	100	150	-	mmho	V_{DS} = -25V, I_D = -400mA
C_{ISS}	Input capacitance	-	85	150	pF	V_{GS} = 0V, V_{DS} = -25V, f = 1.0MHz
C_{OSS}	Common source output capacitance	-	30	85		
C_{RSS}	Reverse transfer capacitance	-	10	35		
$t_{d(ON)}$	Turn-on delay time	-	-	10	ns	V_{DD} = -25V, I_D = -750mA, R_{GEN} = 25Ω
t_r	Rise time	-	-	15		
$t_{d(OFF)}$	Turn-off delay time	-	-	20		
t_f	Fall time	-	-	16		
V_{SD}	Diode forward voltage drop	-	-	-1.8	V	V_{GS} = 0V, I_{SD} = -500mA
t_{rr}	Reverse recovery time	-	300	-	ns	V_{GS} = 0V, I_{SD} = -500mA

Notes:
1. *All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)*
2. *All A.C. parameters sample tested.*

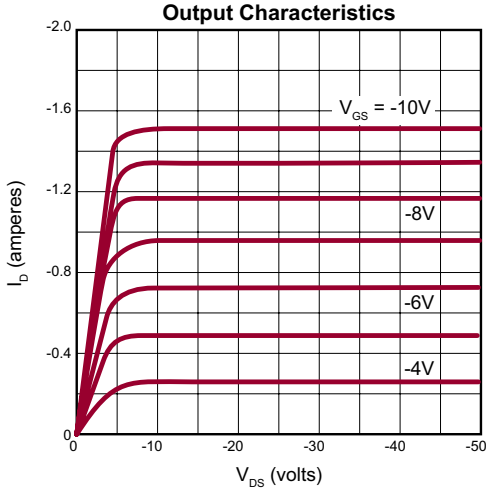
Switching Waveforms and Test Circuit



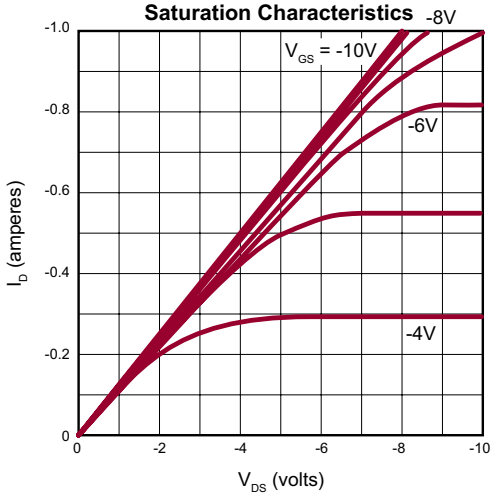


Typical Performance Curves

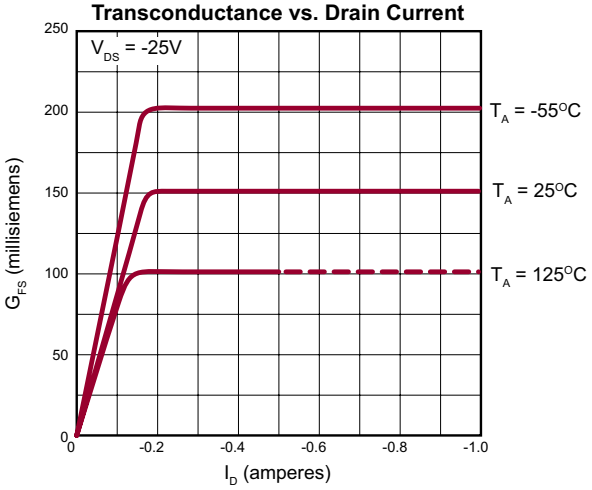
Output Characteristics



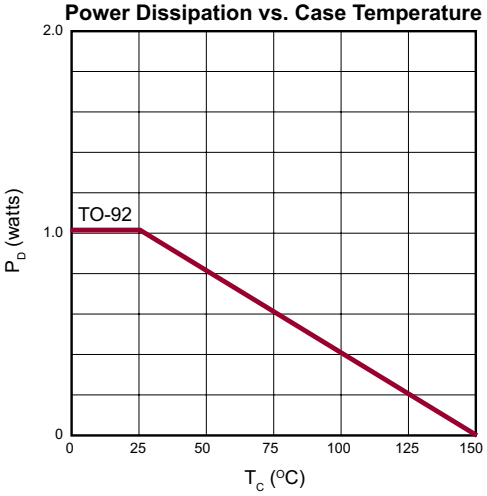
Saturation Characteristics



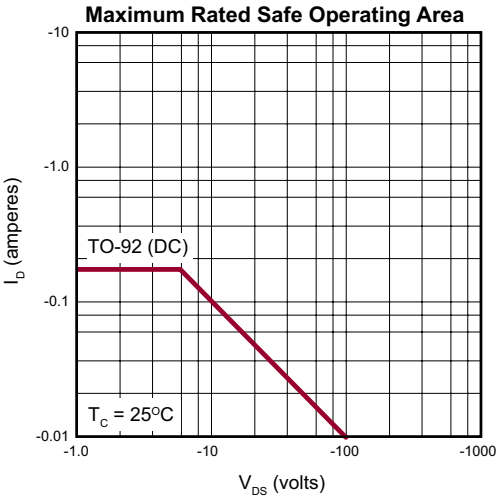
Transconductance vs. Drain Current



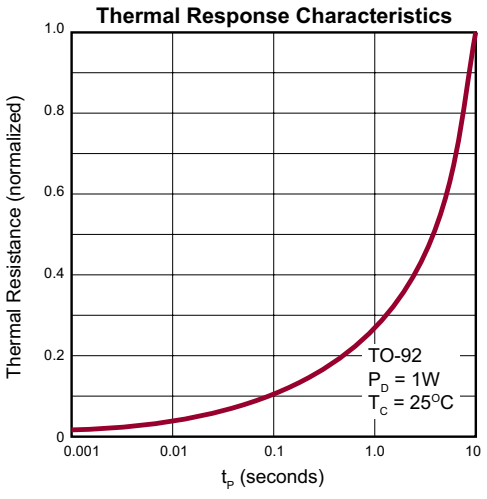
Power Dissipation vs. Case Temperature



Maximum Rated Safe Operating Area

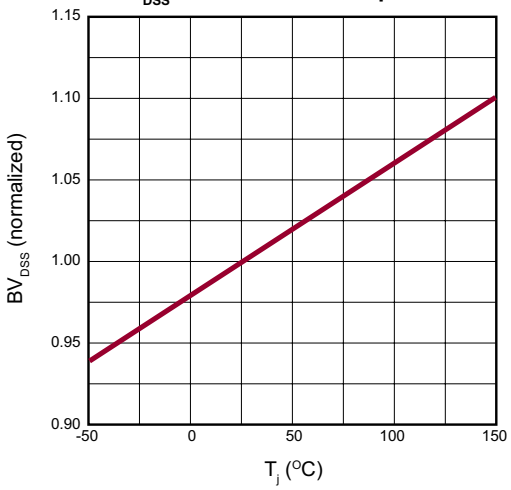


Thermal Response Characteristics

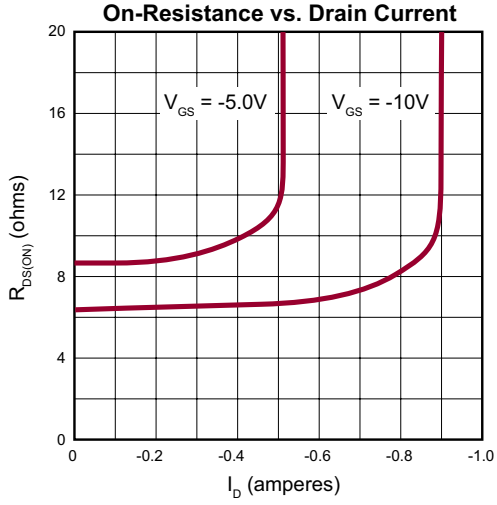


Typical Performance Curves *(cont.)*

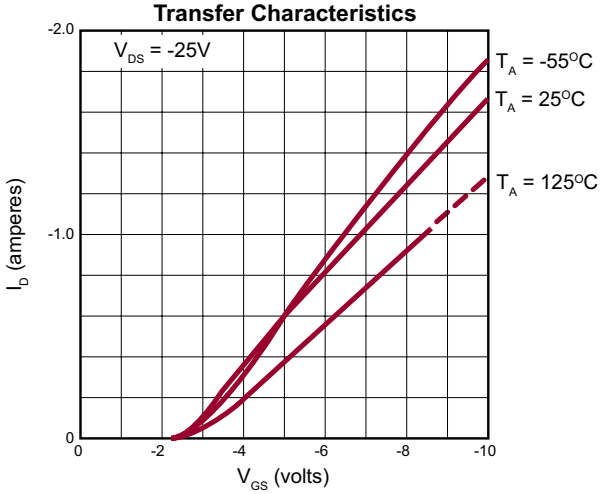
BV_{DSS} Variation with Temperature



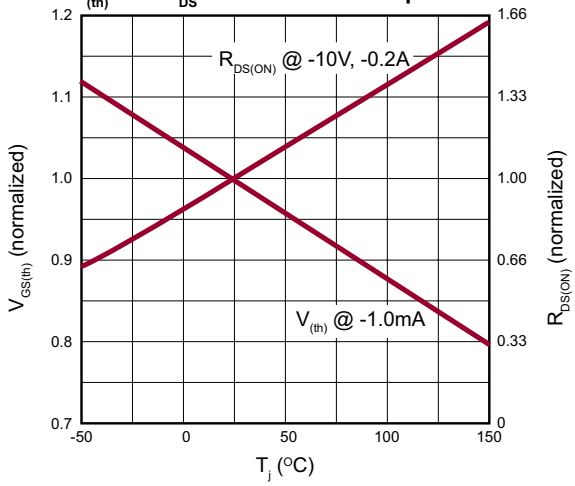
On-Resistance vs. Drain Current



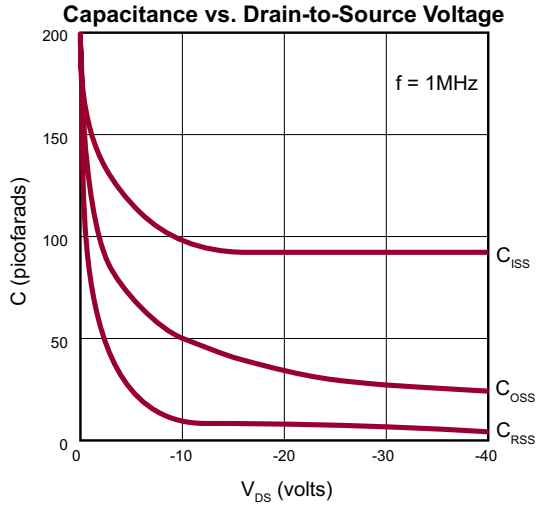
Transfer Characteristics



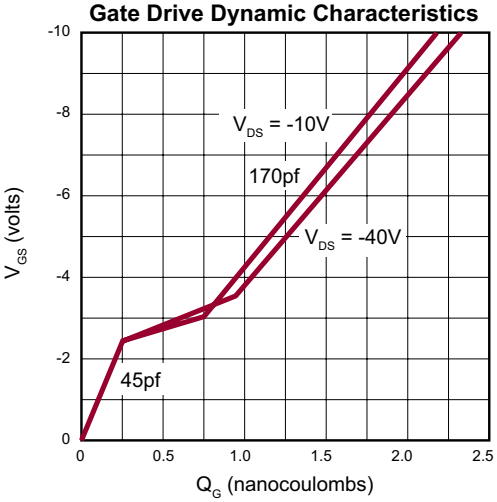
$V_{(th)}$ and R_{DS} Variation with Temperature



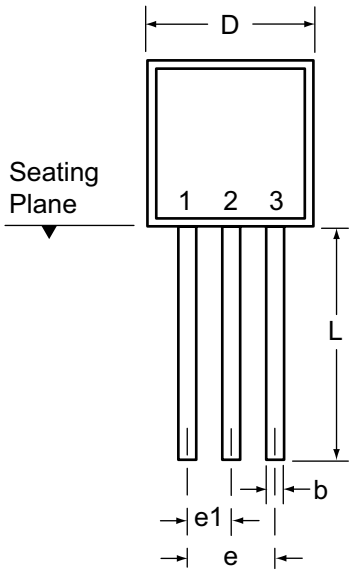
Capacitance vs. Drain-to-Source Voltage



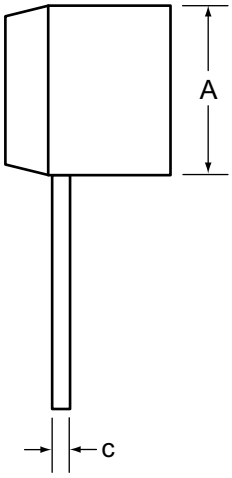
Gate Drive Dynamic Characteristics



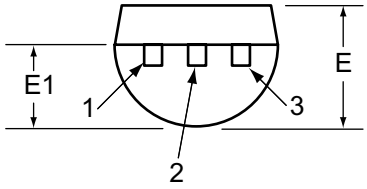
3-Lead TO-92 Package Outline (N3)



Front View



Side View



Bottom View

Symbol		A	b	c	D	E	E1	e	e1	L
Dimensions (inches)	MIN	.170	.014†	.014†	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.
** This dimension is not specified in the JEDEC drawing.*
† This dimension differs from the JEDEC drawing.
Drawings not to scale.
***Supertex Doc.#:** DSPD-3TO92N3, Version E041009.*

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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